

Notice of References Cited	Application/Control No. 10/611,992		Applicant(s)/Patent Under Reexamination RYOU, JAE-HYUN	
	Examiner ARMANDO RODRIGUEZ		Art Unit 2828	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-2004/0161013 a1	08-2004	Bour et al.	372/096
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	M	US-			

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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.